

FEATURES

- Single Gain Set Resistor: G = 1 to 10,000
- **Gain Error: G = 10, 0.08% Max**
- Input Offset Voltage Drift: 0.3µV/°C Max
- Meets IEC 1000-4-2 Level 4 ESD Tests with Two External 5k Resistors
- Gain Nonlinearity: G = 10, 10ppm Max
- Input Offset Voltage: G = 10, 60µV Max
- Input Bias Current: 350pA Max
- PSRR at G = 1: 105dB Min
- CMRR at G = 1: 90dB Min
- Supply Current: 1.3mA Max
- Wide Supply Range: ±2.3V to ±18V
- 1kHz Voltage Noise: 7.5nV/√Hz
- 0.1Hz to 10Hz Noise: 0.28µV_{P-P}
- Available in 8-Pin PDIP and SO Packages

APPLICATIONS

- Bridge Amplifiers
- Strain Gauge Amplifiers
- Thermocouple Amplifiers
- Differential to Single-Ended Converters
- Medical Instrumentation

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TYPICAL APPLICATION

Single Resistor Gain Programmable, Precision Instrumentation Amplifier **DESCRIPTION**

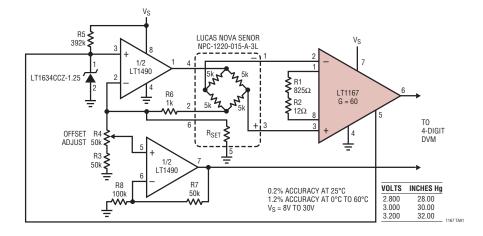
LT1167

The LT®1167 is a low power, precision instrumentation amplifier that requires only one external resistor to set gains of 1 to 10,000. The low voltage noise of 7.5nV/ \sqrt{Hz} (at 1kHz) is not compromised by low power dissipation (0.9mA typical for ±2.3V to ±15V supplies).

The part's high accuracy (10ppm maximum nonlinearity, 0.08% max gain error (G = 10)) is not degraded even for load resistors as low as 2k. The LT1167 is laser trimmed for very low input offset voltage ($40\mu V \max$), drift ($0.3\mu V/^{\circ}C$), high CMRR (90dB, G = 1) and PSRR (105dB, G = 1). Low input bias currents of 350pA max are achieved with the use of superbeta processing. The output can handle capacitive loads up to 1000pF in any gain configuration while the inputs are ESD protected up to 13kV (human body). The LT1167 with two external 5k resistors passes the IEC 1000-4-2 level 4 specification.

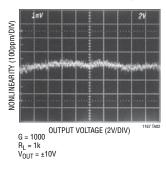
The LT1167, offered in 8-pin PDIP and SO packages, requires significantly less PC board area than discrete multi op amp and resistor designs.

The LT1167-1 offers the same performance as the LT1167, but its input current characteristic at high common mode voltage better supports applications with high input impedance (see the Applications Information section).



Single Supply Barometer

Gain Nonlinearity

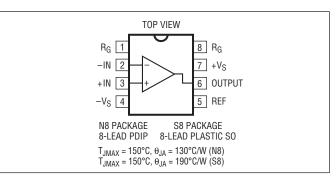


LINEAR TECHNOLOGY

ABSOLUTE MAXIMUM RATINGS

| (Note 1) | |
|---|---------------|
| Supply Voltage | ±20V |
| Differential Input Voltage (Within the | |
| Supply Voltage) | ±40V |
| Input Voltage (Equal to Supply Voltage) | ±20V |
| Input Current (Note 3) | ±20mA |
| Output Short-Circuit Duration | Indefinite |
| Operating Temperature Range | –40°C to 85°C |
| Specified Temperature Range | |
| LT1167AC/LT1167C/ | |
| LT1167AC-1/LT1167C-1 (Note 4) | 0°C to 70°C |
| LT1167AI/LT1167I/ | |
| LT1167AI-1/LT1167I-1 | –40°C to 85°C |
| Storage Temperature Range | 65°C to 150°C |
| Lead Temperature (Soldering, 10 sec) | 300°C |
| | |

PIN CONFIGURATION



ORDER INFORMATION

| LEAD FREE FINISH | TAPE AND REEL | PART MARKING | PACKAGE DESCRIPTION | SPECIFIED TEMPERATURE RANGE |
|-------------------|--------------------|--------------|---------------------|-----------------------------|
| LT1167ACN8#PBF | LT1167ACN8#TRPBF | LT1167AC | 8-Lead PDIP | 0°C to 70°C |
| LT1167ACS8#PBF | LT1167ACS8#TRPBF | 1167A | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167AIN8#PBF | LT1167AIN8#TRPBF | LT1167AI | 8-Lead PDIP | -40°C to 85°C |
| LT1167AIS8#PBF | LT1167AIS8#TRPBF | 1167AI | 8-Lead Plastic SO | -40°C to 85°C |
| LT1167CN8#PBF | LT1167CN8#TRPBF | LT1167C | 8-Lead PDIP | 0°C to 70°C |
| LT1167CS8#PBF | LT1167CS8#TRPBF | 1167 | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167IN8#PBF | LT1167IN8#TRPBF | LT11671 | 8-Lead PDIP | -40°C to 85°C |
| LT1167IS8#PBF | LT1167IS8#TRPBF | 11671 | 8-Lead Plastic SO | -40°C to 85°C |
| LT1167CS8-1#PBF | LT1167CS8-1#TRPBF | 11671 | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167IS8-1#PBF | LT1167IS8-1#TRPBF | 11671 | 8-Lead Plastic SO | -40°C to 85°C |
| LT1167ACS8-1#PBF | LT1167ACS8-1#TRPBF | 11671 | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167AIS8-1#PBF | LT1167AIS8-1#TRPBF | 11671 | 8-Lead Plastic SO | -40°C to 85°C |
| LEAD BASED FINISH | TAPE AND REEL | PART MARKING | PACKAGE DESCRIPTION | SPECIFIED TEMPERATURE RANGE |
| LT1167ACN8 | LT1167ACN8#TR | LT1167AC | 8-Lead PDIP | 0°C to 70°C |
| LT1167ACS8 | LT1167ACS8#TR | 1167A | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167AIN8 | LT1167AIN8#TR | LT1167AI | 8-Lead PDIP | –40°C to 85°C |
| LT1167AIS8 | LT1167AIS8#TR | 1167AI | 8-Lead Plastic SO | –40°C to 85°C |
| LT1167CN8 | LT1167CN8#TR | LT1167C | 8-Lead PDIP | 0°C to 70°C |
| LT1167CS8 | LT1167CS8#TR | 1167 | 8-Lead Plastic SO | 0°C to 70°C |
| LT1167IN8 | LT1167IN8#TR | LT11671 | 8-Lead PDIP | –40°C to 85°C |
| LT1167IS8 | LT1167IS8#TR | 11671 | 8-Lead Plastic SO | –40°C to 85°C |

Consult LTC Marketing for parts specified with wider operating temperature ranges. *The temperature grade is identified by a label on the shipping container. Consult LTC Marketing for information on non-standard lead based finish parts.

For more information on lead free part marking, go to: http://www.linear.com/leadfree/ For more information on tape and reel specifications, go to: http://www.linear.com/tapeandreel/



ELECTRICAL CHARACTERISTICS $V_{s} = \pm 15V$, $V_{CM} = 0V$, $T_{A} = 25^{\circ}C$, $R_{L} = 2k$, unless otherwise noted.

| | | | LT1167# | 7AC/LTC1 \C-1/LTC1 | 167AI-1 | LT1167 | 67C/LTC1 /C-1/LTC1 | 1671-1 | |
|-----------------------|---|---|--|----------------------------------|--|--|----------------------------------|--|---|
| SYMBOL | PARAMETER | CONDITIONS (NOTE 7) | MIN | ТҮР | MAX | MIN | ТҮР | MAX | UNITS |
| G | Gain Range | $G = 1 + (49.4 \text{k/R}_{G})$ | 1 | | 10k | 1 | | 10k | |
| | Gain Error | G = 1 G = 10 (Note 2) G = 100 (Note 2) G = 1000 (Note 2) | | 0.008 0.010 0.025 0.049 | 0.02 0.08 0.08 0.10 | | 0.015 0.020 0.030 0.040 | 0.03 0.10 0.10 0.10 | % % % |
| | Gain Nonlinearity (Note 5) | $V_0 = \pm 10V$, G = 1 $V_0 = \pm 10V$, G = 10 and 100 $V_0 = \pm 10V$, G = 1000 | | 1 2 15 | 6 10 40 | | 1.5 3 20 | 10 15 60 | ppm ppm ppm |
| | | | | 5 6 20 | 12 15 65 | | 6 7 25 | 15 20 80 | ppm ppm ppm |
| V _{OST} | Total Input Referred Offset Voltage | $V_{0ST} = V_{0SI} + V_{0S0}/G$ | | 20 | | | 20 | | ppm |
| V _{OSI} | Input Offset Voltage | $G = 1000, V_S = \pm 5V \text{ to } \pm 15V$ | | 15 | 40 | | 20 | 60 | μV |
| V _{0S0} | Output Offset Voltage | $G = 1, V_S = \pm 5V \text{ to } \pm 15V$ | | 40 | 200 | | 50 | 300 | μV |
| I _{OS} | Input Offset Current | | | 90 | 320 | | 100 | 450 | pA |
| IB | Input Bias Current | | | 50 | 350 | | 80 | 500 | pA |
| e _n | Input Noise Voltage (Note 8) | 0.1Hz to 10Hz, G = 1 0.1Hz to 10Hz, G = 10 0.1Hz to 10Hz, G = 100 and 1000 | | 2.00 0.50 0.28 | | | 2.00 0.50 0.28 | | μV _{P-P} μV _{P-P} μV _{P-P} |
| Total RTI | Noise = $\sqrt{e_{ni}^2 + (e_{no}/G)^2}$ (Note 8) | | | | | | | | |
| e _{ni} | Input Noise Voltage Density (Note 8) | f ₀ = 1kHz | | 7.5 | 12 | | 7.5 | 12 | nV/√Hz |
| e _{no} | Output Noise Voltage Density (Note 8) | f ₀ = 1kHz (Note 3) | | 67 | 90 | | 67 | 90 | nV/√Hz |
| i _n | Input Noise Current | f ₀ = 0.1Hz to 10Hz | | 10 | | | 10 | | pA _{P-P} |
| | Input Noise Current Densty | f ₀ = 10Hz | | 124 | | | 124 | | fA/√Hz |
| R _{IN} | Input Resistance | $V_{IN} = \pm 10V$ | 200 | 1000 | | 200 | 1000 | | GΩ |
| C _{IN(DIFF)} | Differential Input Capacitance | f ₀ = 100kHz | | 1.6 | | | 1.6 | | pF |
| C _{IN(CM)} | Common Mode Input Capacitance | f ₀ = 100kHz | | 1.6 | | | 1.6 | | pF |
| V _{CM} | Input Voltage Range | $ \begin{array}{l} G = 1, \mbox{ Other Input Grounded} \\ V_S = \pm 2.3V \mbox{ to } \pm 5V \\ V_S = \pm 5V \mbox{ to } \pm 18V \end{array} $ | -V _S +1.9 -V _S +1.9 | | +V _S -1.2 +V _S -1.4 | -V _S +1.9 -V _S +1.9 | | +V _S -1.2 +V _S -1.4 | V V |
| CMRR | Common Mode Rejection Ratio | $ 1k Source Imbalance, \\ V_{CM} = 0V to \pm 10V \\ G = 1 \\ G = 10 \\ G = 100 \\ G = 1000 $ | 90 106 120 126 | 95 115 125 140 | | 85 100 110 120 | 95 115 125 140 | | dB dB dB dB |
| PSRR | Power Supply Rejection Ratio | $V_{S} = \pm 2.3V \text{ to } \pm 18V$ G = 1 G = 10 G = 100 G = 1000 | 105 125 131 135 | 120 135 140 150 | | 100 120 126 130 | 120 135 140 150 | | dB dB dB dB |
| I _S | Supply Current | V _S = ±2.3V to ±18V | | 0.9 | 1.3 | | 0.9 | 1.3 | mA |
| V _{OUT} | Output Voltage Swing | $ \begin{array}{l} R_{L} = 10k \\ V_{S} = \pm 2.3 V \text{ to } \pm 5 V \\ V_{S} = \pm 5 V \text{ to } \pm 18 V \end{array} $ | -V _S +1.1 -V _S +1.2 | | +V _S -1.2 +V _S -1.3 | -V _S +1.1 -V _S +1.2 | | +V _S -1.2 +V _S -1.3 | V V |
| | 1 | | | | - | - | | - | 1167fc |



ELECTRICAL CHARACTERISTICS $V_{S} = \pm 15V$, $V_{CM} = 0V$, $T_{A} = 25^{\circ}C$, $R_{L} = 2k$, unless otherwise noted.

| SYMBOL | PARAMETER | CONDITIONS (NOTE 7) | | 67AC/LTC1 AC-1/LTC1 TYP | | | 67C/LTC1 ⁻ 7C-1/LTC1 ⁻ TYP | - | UNITS |
|--------------------|----------------------------|--|----------------------|-------------------------------|----------------------|----------------------|--|----------------------|--------------------------|
| I _{OUT} | Output Current | | 20 | 27 | | 20 | 27 | | mA |
| BW | Bandwidth | G = 1 G = 10 G = 100 G = 1000 | | 1000 800 120 12 | | | 1000 800 120 12 | | kHz kHz kHz kHz |
| SR | Slew Rate | $G = 1, V_{OUT} = \pm 10V$ | 0.75 | 1.2 | | 0.75 | 1.2 | | V/µs |
| | Settling Time to 0.01% | 10V Step G = 1 to 100 G = 1000 | | 14 130 | | | 14 130 | | μs µs |
| R _{REFIN} | Reference Input Resistance | | | 20 | | | 20 | | kΩ |
| I _{REFIN} | Reference Input Current | V _{REF} = 0V | | 50 | | | 50 | | μA |
| V _{REF} | Reference Voltage Range | | -V _S +1.6 | | +V _S -1.6 | -V _S +1.6 | | +V _S -1.6 | V |
| A _{VREF} | Reference Gain to Output | | | 1 ±0.0001 | | | 1 ±0.0001 | | |

The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at T_A = 25°C. V_S = ±15V, V_{CM} = 0V, 0°C \leq T_A \leq 70°C, R_L = 2k, unless otherwise noted.

| | | | LT1167AC/LT1167AC-1 | | | LT1167C/LT1167C-1 | | | |
|--|--|---|---|--|--|--|--|---|--|
| PARAMETER | CONDITIONS (NOTE 7) | | MIN | TYP | MAX | MIN | ТҮР | MAX | UNITS |
| Gain Error | G = 1 G = 10 (Note 2) G = 100 (Note 2) G = 1000 (Note 2) | • • • | | 0.01 0.08 0.09 0.14 | 0.03 0.30 0.30 0.33 | | 0.012 0.100 0.120 0.140 | 0.04 0.33 0.33 0.35 | % % % |
| Gain Nonlinearity | $V_{OUT} = \pm 10V, G = 1$ $V_{OUT} = \pm 10V, G = 10 \text{ and } 100$ $V_{OUT} = \pm 10V, G = 1000$ | • | | 1.5 3 20 | 10 15 60 | | 3 4 25 | 15 20 80 | ppm ppm ppm |
| Gain vs Temperature | G < 1000 (Note 2) | ٠ | | 20 | 50 | | 20 | 50 | ppm/°C |
| Total Input Referred Offset Voltage | $V_{OST} = V_{OSI} + V_{OSO}/G$ | | | | | | | | |
| Input Offset Voltage | $V_{S} = \pm 5V \text{ to } \pm 15V$ | | | 18 | 60 | | 23 | 80 | μV |
| Input Offset Voltage Hysteresis | (Notes 3, 6) | | | 3.0 | | | 3.0 | | μV |
| Output Offset Voltage | $V_{S} = \pm 5V$ to $\pm 15V$ | | | 60 | 380 | | 70 | 500 | μV |
| Output Offset Voltage Hysteresis | (Notes 3, 6) | | | 30 | | | 30 | | μV |
| Input Offset Drift (Note 8) | (Note 3) | | | 0.05 | 0.3 | | 0.06 | 0.4 | μV/°C |
| Output Offset Drift | (Note 3) | | | 0.7 | 3 | | 0.8 | 4 | μV/°C |
| Input Offset Current | | | | 100 | 400 | | 120 | 550 | pА |
| Input Offset Current Drift | | • | | 0.3 | | | 0.4 | | pA/°C |
| Input Bias Current | | • | | 75 | 450 | | 105 | 600 | pА |
| Input Bias Current Drift | | | | 0.4 | | | 0.4 | | pA/°C |
| Input Voltage Range | | • | -V _S +2.1 -V _S +2.1 | | +V _S -1.3 +V _S -1.4 | -V _S +2.1 -V _S +2.1 | | +V _S -1.3 +V _S -1.4 | V V |
| Common Mode Rejection Ratio | $\begin{array}{l} 1k \ \text{Source Imbalance,} \\ V_{CM} = 0V \ \text{to } \pm 10V \\ \text{G} = 1 \\ \text{G} = 10 \\ \text{G} = 100 \\ \text{G} = 1000 \end{array}$ | • | 88 100 115 117 | 92 110 120 135 | | 83 97 113 114 | 92 110 120 135 | | dB dB dB dB 1167fc |
| | Gain Error Gain Nonlinearity Gain vs Temperature Total Input Referred Offset Voltage Input Offset Voltage Hysteresis Output Offset Voltage Hysteresis Output Offset Voltage Hysteresis Input Offset Drift (Note 8) Output Offset Drift (Note 8) Output Offset Current Input Offset Current Input Offset Current Input Bias Current Input Bias Current Drift Input Bias Current Drift Input Voltage Range | Gain Error $G = 1$ $G = 10 (Note 2)$ $G = 100 (Note 2)$ $G = 1000 (Note 2)$ Gain Nonlinearity $V_{OUT} = \pm 10V, G = 1$ $V_{OUT} = \pm 10V, G = 10 and 100V_{OUT} = \pm 10V, G = 1000Gain vs TemperatureG < 1000 (Note 2)Total Input ReferredOffset VoltageV_{S} = \pm 5V \text{ to } \pm 15VInput Offset VoltageV_S = \pm 5V \text{ to } \pm 15VInput Offset Voltage Hysteresis(Notes 3, 6)Output Offset Voltage Hysteresis(Notes 3, 6)Output Offset Drift (Note 8)(Note 3)Output Offset Drift (Note 8)(Note 3)Input Offset CurrentInput Offset CurrentInput Offset Current DriftInput Bias Current DriftInput Bias Current DriftG = 1, Other Input GroundedV_S = \pm 5V \text{ to } \pm 18VCommon Mode Rejection Ratio1k Source Imbalance,V_{CM} = 0V \text{ to } \pm 10VG = 1G = 100$ | Gain Error $G = 1$ $G = 10$ (Note 2) $G = 100$ (Note 2) $G = 1000$ (Note 2)Gain Nonlinearity $V_{OUT} = \pm 10V$, $G = 1$ $V_{OUT} = \pm 10V$, $G = 10$ and 100 $V_{OUT} = \pm 10V$, $G = 10$ and 100 $V_{OUT} = \pm 10V$, $G = 10$ and 100 $V_{OUT} = \pm 10V$, $G = 1000$ Gain vs Temperature $G < 1000$ (Note 2)Total Input Referred Offset Voltage $V_{OST} = V_{OSI} + V_{OSO}/G$ Input Offset Voltage $V_S = \pm 5V$ to $\pm 15V$ Input Offset Voltage Hysteresis(Notes 3, 6)Output Offset Voltage Hysteresis(Notes 3, 6)Input Offset Drift (Note 8)(Note 3)Output Offset Current \bullet Input Offset Current Drift \bullet Input Bias Current Drift \bullet Input Bias Current Drift \bullet Input Voltage Range $G = 1, Other Input Grounded$ $V_S = \pm 5V$ to $\pm 18V$ Common Mode Rejection Ratio1k Source Imbalance, $V_{CM} = 0V$ to $\pm 10V$ $G = 10$ $G = 100$ | PARAMETERCONDITIONS (NOTE 7)MINGain Error $G = 1$ $G = 10 (Note 2)$ $G = 100 (Note 2)$ $G = 1000 (Note 2)$ •Gain Nonlinearity $V_{OUT} = \pm 10V$, $G = 1$ $V_{OUT} = \pm 10V$, $G = 10$ and 100 $V_{OUT} = \pm 10V$, $G = 10$ and 100 $V_{OUT} = \pm 10V$, $G = 1000$ Gain vs Temperature $G < 1000 (Note 2)$ Gain vs Temperature $G < 1000 (Note 2)$ Total Input Referred Offset Voltage $V_S = \pm 5V \text{ to } \pm 15V$ Input Offset Voltage $V_S = \pm 5V \text{ to } \pm 15V$ Input Offset Voltage Hysteresis(Notes 3, 6)Output Offset Voltage Hysteresis(Notes 3, 6)Input Offset Drift (Note 8)(Note 3)Output Offset Drift (Note 8)(Note 3)Output Offset Current•Input Offset Current Drift•Input Bias Current Drift•Input Bias Current Drift•Input Bias Current Drift•Input Voltage Range $G = 1, 0 \text{ ther Input Grounded}$ $V_S = \pm 5V \text{ to } \pm 18V$ $V_{CM} = 0V \text{ to } \pm 10V$ $G = 1$ • $Bas G = 10$ $G = 100$ • $Bas G = 10$ $G = 100$ • | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | PARAMETER CONDITIONS (NOTE 7) MIN TYP MAX Gain Error G = 1 G = 10 (Note 2) G = 100 (Note 2) 0.01 0.03 0.09 0.30 0.09 0.30 0.09 0.30 0.09 0.30 0.09 0.30 0.14 0.33 0.14 0.33 15 0 0.01 20 60 6 1000 (Note 2) 0.14 0.33 15 0 0.01 20 60 6 3 15 0 0.01 20 60 6 6 15 10 0.05 0.31 15 0 0.05 0.05 0.05 0.05 0.05 0.05 0.05 0.05 0.30 0 0.014 0.03 6 100 400 10 400 18 60 380 0 0.05 0.3 0.30 10 10 400 10 400 10 400 10 400 10 400 10 400 10 400 10 400 100 400 10 400 10 <td>$\begin{array}{ c c c c c c c c c c c c c c c c c c c$</td> <td>PARAMETER CONDITIONS (NOTE 7) MIN TYP MAX MIN TYP Gain Error $G = 10$ (Note 2) G = 100 (Note 2) G = 100 (Note 2) G = 1000 (Note 2) • 0.01 0.03 0.030 0.012 0.030 0.0100 Gain Nonlinearity $V_{OUT} = \pm 10V, G = 1$ $V_{OUT} = \pm 10V, G = 10$ and 100 $V_{OUT} = \pm 10V, G = 1000$ • 1.5 10 3 Gain vs Temperature G < 1000 (Note 2)</td> • 20 50 20 Total Input Referred Offset Voltage VS = $\pm 5V$ to $\pm 15V$ • 18 60 23 Input Offset Voltage VS = $\pm 5V$ to $\pm 15V$ • 18 60 23 Input Offset Voltage VS = $\pm 5V$ to $\pm 15V$ • 18 60 23 Input Offset Voltage VS = $\pm 5V$ to $\pm 15V$ • 18 60 23 Input Offset Voltage Hysteresis (Notes 3, 6) 3.0 3.0 3.0 3.0 Output Offset Drift (Note 8) (Note 3) 0.07 3 0.8 0.07 3 | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ | PARAMETER CONDITIONS (NOTE 7) MIN TYP MAX MIN TYP Gain Error $G = 10$ (Note 2) G = 100 (Note 2) G = 100 (Note 2) G = 1000 (Note 2) • 0.01 0.03 0.030 0.012 0.030 0.0100 Gain Nonlinearity $V_{OUT} = \pm 10V, G = 1$ $V_{OUT} = \pm 10V, G = 10$ and 100 $V_{OUT} = \pm 10V, G = 1000$ • 1.5 10 3 Gain vs Temperature G < 1000 (Note 2) | $\begin{array}{ c c c c c c c c c c c c c c c c c c c$ |



ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at T_A = 25°C. V_S = ±15V, V_{CM} = 0V, 0°C \leq T_A \leq 70°C, R_L = 2k, unless otherwise noted.

| | | | | LT1167 | LT1167AC/LT1167AC-1 | | | LT1167C/LT1167C-1 | | | |
|------------------|------------------------------|--|---|--|--------------------------|--|-------------------------|--------------------------|--|----------------------|--|
| SYMBOL | PARAMETER | CONDITIONS (NOTE 7) | | MIN | TYP | MAX | MIN | ТҮР | MAX | UNITS | |
| PSRR | Power Supply Rejection Ratio | $V_{S} = \pm 2.3V \text{ to } \pm 18V$ G = 1 G = 10 G = 100 G = 1000 | • | 103 123 127 129 | 115 130 135 145 | | 98 118 124 126 | 115 130 135 145 | | dB dB dB dB | |
| Is | Supply Current | $V_{\rm S} = \pm 2.3 \text{V} \text{ to } \pm 18 \text{V}$ | • | | 1.0 | 1.5 | | 1.0 | 1.5 | mA | |
| V _{OUT} | Output Voltage Swing | | • | -V _S +1.4 -V _S +1.6 | | +V _S -1.3 +V _S -1.5 | | | +V _S -1.3 +V _S -1.5 | V V | |
| I _{OUT} | Output Current | | • | 16 | 21 | | 16 | 21 | | mA | |
| SR | Slew Rate | $G = 1, V_{OUT} = \pm 10V$ | • | 0.65 | 1.1 | | 0.65 | 1.1 | | V/µs | |
| V _{REF} | REF Voltage Range | (Note 3) | | -V _S +1.6 | | +V _S -1.6 | -V _S +1.6 | | +V _S -1.6 | V | |

The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $T_A = 25^{\circ}C$. $V_S = \pm 15V$, $V_{CM} = 0V$, $-40^{\circ}C \le T_A \le 85^{\circ}C$, $R_L = 2k$, unless otherwise noted.

| | | | | LT1167AI/LT1167AI-1 | | | LT11 | | | |
|---------------------|--|--|-------------|--|----------------------------------|--|--|----------------------------------|--|----------------------|
| SYMBOL | PARAMETER | CONDITIONS (NOTE 7) | | MIN | TYP | MAX | MIN | ТҮР | MAX | UNITS |
| | Gain Error | G = 1 G = 10 (Note 2) G = 100 (Note 2) G = 1000 (Note 2) | • • • | | 0.014 0.130 0.140 0.160 | 0.04 0.40 0.40 0.40 | | 0.015 0.140 0.150 0.180 | 0.05 0.42 0.42 0.45 | % % % |
| G _N | Gain Nonlinearity (Notes 2, 4) | $V_0 = \pm 10V$, G = 1 $V_0 = \pm 10V$, G = 10 and 100 $V_0 = \pm 10V$, G = 1000 | • | | 2 5 26 | 15 20 70 | | 3 6 30 | 20 30 100 | ppm ppm ppm |
| G/T | Gain vs Temperature | G < 1000 (Note 2) | • | | 20 | 50 | | 20 | 50 | ppm/°C |
| V _{OST} | Total Input Referred Offset Voltage | $V_{OST} = V_{OSI} + V_{OSO}/G$ | | | | | | | | |
| V _{OSI} | Input Offset Voltage | | • | | 20 | 75 | | 25 | 100 | μV |
| V _{OSIH} | Input Offset Voltage Hysteresis | (Notes 3, 6) | | | 3.0 | | | 3.0 | | μV |
| V _{OSO} | Output Offset Voltage | | • | | 180 | 500 | | 200 | 600 | μV |
| V _{OSOH} | Output Offset Voltage Hysteresis | (Notes 3, 6) | | | 30 | | | 30 | | μV |
| V _{OSI} /T | Input Offset Drift (Note 8) | (Note 3) | | | 0.05 | 0.3 | | 0.06 | 0.4 | µV/°C |
| V _{OSO} /T | Output Offset Drift | (Note 3) | • | | 0.8 | 5 | | 1 | 6 | µV/°C |
| l _{os} | Input Offset Current | | | | 110 | 550 | | 120 | 700 | pА |
| I _{OS} /T | Input Offset Current Drift | | | | 0.3 | | | 0.3 | | pA/°C |
| I _B | Input Bias Current | | | | 180 | 600 | | 220 | 800 | pА |
| I _B /T | Input Bias Current Drift | | | | 0.5 | | | 0.6 | | pA/°C |
| V _{CM} | Input Voltage Range | | • | -V _S +2.1 -V _S +2.1 | | +V _S -1.3 +V _S -1.4 | -V _S +2.1 -V _S +2.1 | | +V _S -1.3 +V _S -1.4 | V V |
| CMRR | Common Mode Rejection Ratio | $\begin{array}{l} 1k \mbox{ Source Imbalance,} \\ V_{CM} = 0V \mbox{ to } \pm 10V \\ G = 1 \\ G = 10 \\ G = 100 \\ G = 1000 \end{array}$ | • | 86 98 114 116 | 90 105 118 133 | | 81 95 112 112 | 90 105 118 133 | | dB dB dB dB |



ELECTRICAL CHARACTERISTICS The \bullet denotes the specifications which apply over the full operating temperature range, otherwise specifications are at T_A = 25°C. V_S = ±15V, V_{CM} = 0V, 0°C \leq T_A \leq 70°C, R_L = 2k, unless otherwise noted.

| | | | LT116 | 7AI/LT11 | 67AI-1 | LT1167I/LT1167I-1 | | | | |
|------------------|------------------------------|--|-------|--|--------------------------|--|-------------------------|--------------------------|--|----------------------|
| SYMBOL | PARAMETER | CONDITIONS (NOTE 7) | | MIN | TYP | MAX | MIN | ТҮР | MAX | UNITS |
| PSRR | Power Supply Rejection Ratio | $V_{S} = \pm 2.3V \text{ to } \pm 18V$ G = 1 G = 10 G = 100 G = 1000 | • | 100 120 125 128 | 112 125 132 140 | | 95 115 120 125 | 112 125 132 140 | | dB dB dB dB |
| I _S | Supply Current | | ٠ | | 1.1 | 1.6 | | 1.1 | 1.6 | mA |
| V _{OUT} | Output Voltage Swing | $V_{S} = \pm 2.3V \text{ to } \pm 5V$ $V_{S} = \pm 5V \text{ to } \pm 18V$ | • | -V _S +1.4 -V _S +1.6 | | +V _S -1.3 +V _S -1.5 | | | +V _S -1.3 +V _S -1.5 | V V |
| I _{OUT} | Output Current | | ٠ | 15 | 20 | | 15 | 20 | | mA |
| SR | Slew Rate | $G = 1, V_{OUT} = \pm 10V$ | • | 0.55 | 0.95 | | 0.55 | 0.95 | | V/µs |
| V _{REF} | REF Voltage Range | (Note 3) | ٠ | -V _S +1.6 | | +V _S -1.6 | -V _S +1.6 | | +V _S -1.6 | V |

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

Note 2: Does not include the effect of the external gain resistor RG.

Note 3: This parameter is not 100% tested.

Note 4: The LT1167AC/LT1167C/LT1167AC-1/LT1167C-1 are designed, characterized and expected to meet the industrial temperature limits, but are not tested at -40°C and 85°C. I-grade parts are guaranteed.

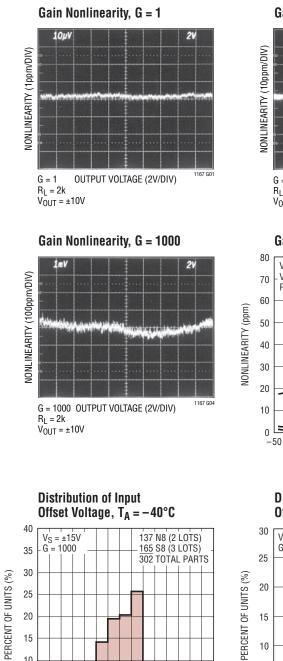
Note 5: This parameter is measured in a high speed automatic tester that does not measure the thermal effects with longer time constants. The magnitude of these thermal effects are dependent on the package used, heat sinking and air flow conditions.

Note 6: Hysteresis in offset voltage is created by package stress that differs depending on whether the IC was previously at a higher or lower temperature. Offset voltage hysteresis is always measured at 25°C, but the IC is cycled to 85°C I-grade (or 70°C C-grade) or -40°C I-grade (0°C C-grade) before successive measurement. 60% of the parts will pass the typical limit on the data sheet.

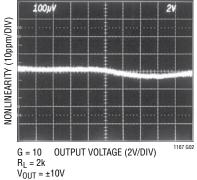
Note 7: Typical parameters are defined as the 60% of the yield parameter distribution.

Note 8: Referred to input.





Gain Nonlinearity, G = 10



Gain Nonlinearity vs Temperature

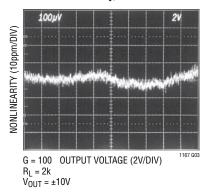
 $V_S = \pm 15V$ V_{OUT} = -10V TO 10V _

 $R_L = 2k$

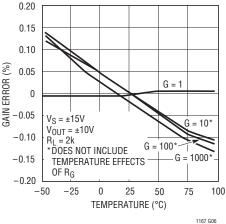
-25

0

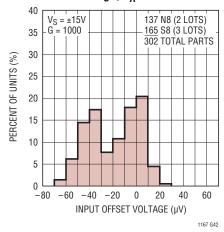
Gain Nonlinearity, G = 100



Gain Error vs Temperature



Distribution of Input Offset Voltage, $T_A = 85^{\circ}C$



1167 G05

20 15 10 5 0 0 60 -80 -60 -40 -20 20 40

INPUT OFFSET VOLTAGE (µV)

1167 G40

Distribution of Input Offset Voltage, $T_A = 25^{\circ}C$

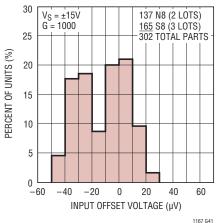
G = 1000

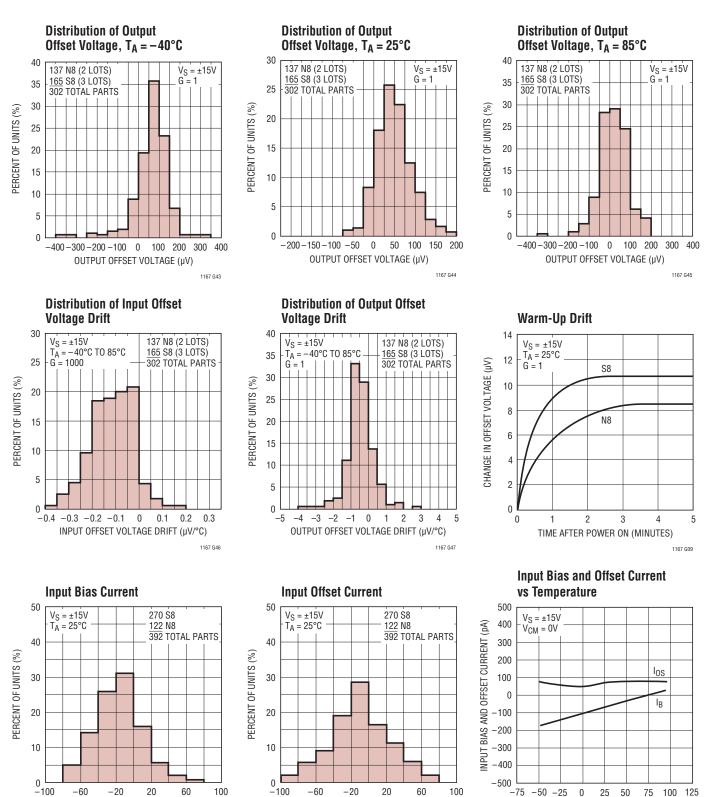
G = 100

25 50 75 100 150

TEMPERATURE (°C)

G = 1, 10





INPUT OFFSET CURRENT (pA)

1167 G11

1167 G12

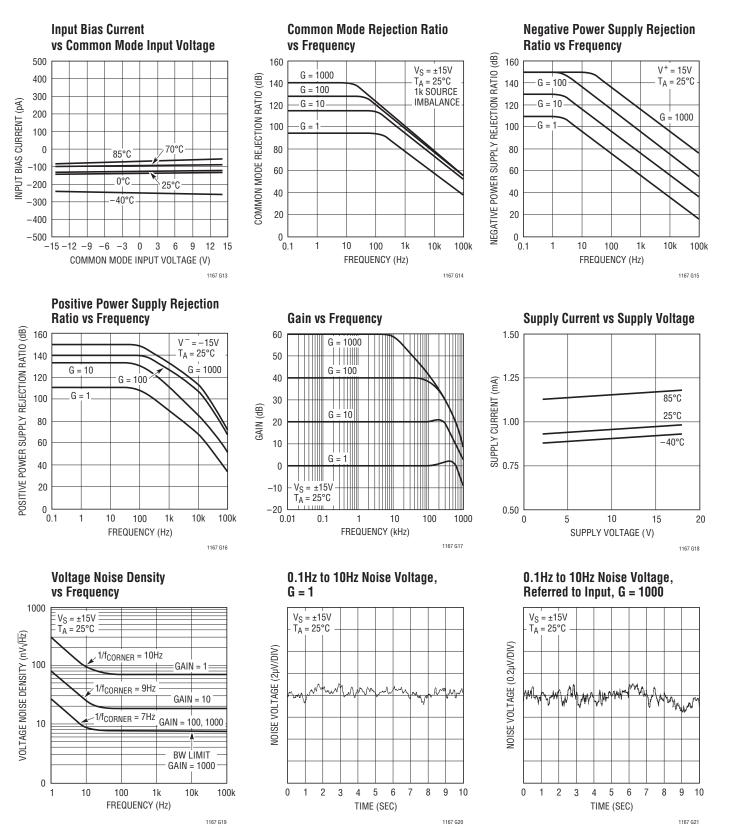


TEMPERATURE (°C)

INPUT BIAS CURRENT (pA)

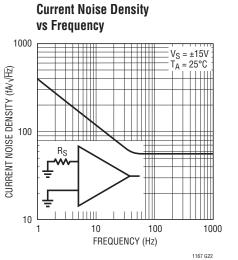
1167 G10

¹¹⁶⁷fc









 $V_{\rm S} = \pm 15V$ $T_A = 25^{\circ}C$ CURRENT NOISE (5pA/DIV) \mathfrak{P}_1 mum N MAN MA 2 3 7 8 0 1 4 5 6 9 10 TIME (SEC)

Large-Signal Transient Response

5V/DIV

G = 1

 $V_{S} = \pm 15V$

 $C_1 = 60 pF$

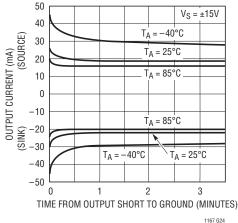
 $R_L = 2k$

1167 G23

1167 G28

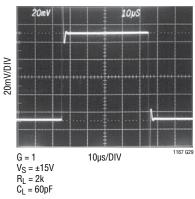
0.1Hz to 10Hz Current Noise

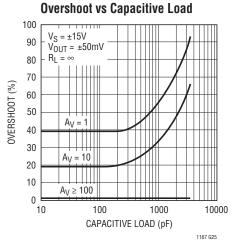


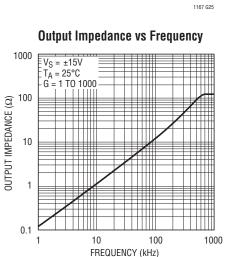


1107 62



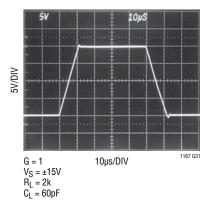




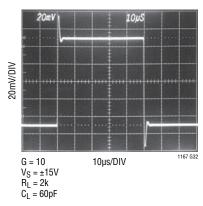


Large-Signal Transient Response

10µs/DIV



Small-Signal Transient Response

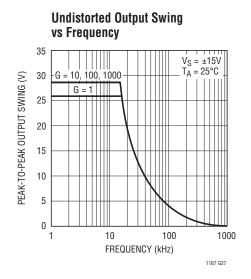




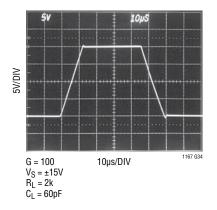


1167 G26

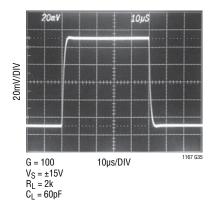




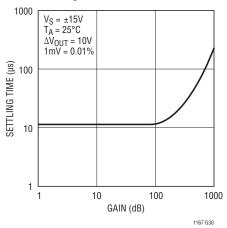
Large-Signal Transient Response



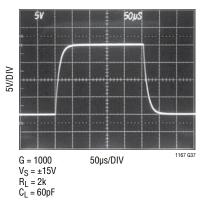
Small-Signal Transient Response



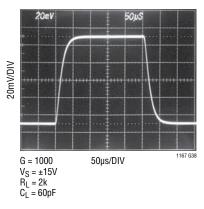
Settling Time vs Gain

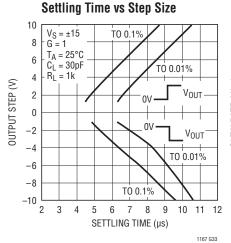


Large-Signal Transient Response



Small-Signal Transient Response



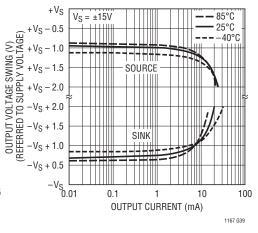


1.8 V_S = ±15V $V_{OUT} = \pm 10V$ G = 1 1.6 SLEW RATE (V/µs) 1.4 +SLEW 1.2 SLEW 1.0 0.8 -50 -25 0 25 50 75 100 125 TEMPERATURE (°C)

1167 636

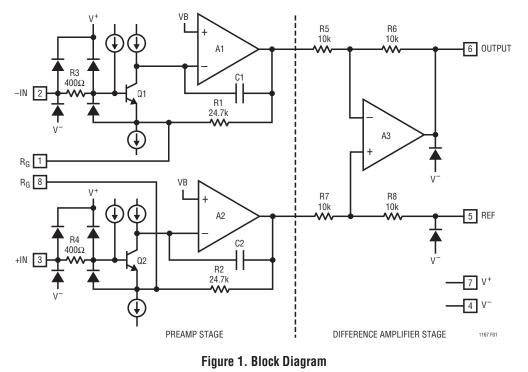
Slew Rate vs Temperature

Output Voltage Swing vs Load Current





BLOCK DIAGRAM



THEORY OF OPERATION

The LT1167 is a modified version of the three op amp instrumentation amplifier. Laser trimming and monolithic construction allow tight matching and tracking of circuit parameters over the specified temperature range. Refer to the block diagram (Figure 1) to understand the following circuit description. The collector currents in Q1 and Q2 are trimmed to minimize offset voltage drift, thus assuring a high level of performance. R1 and R2 are trimmed to an absolute value of 24.7k to assure that the gain can be set accurately (0.05% at G = 100) with only one external resistor R_G . The value of R_G determines the transconductance of the preamp stage. As R_G is reduced for larger programmed gains, the transconductance of the input preamp stage increases to that of the input transistors Q1 and Q2. This increases the open-loop gain when the programmed gain is increased, reducing the input referred gain related errors and noise. The input voltage noise at gains greater than 50 is determined only by Q1 and Q2. At lower gains the noise of the difference amplifier and preamp gain setting resistors increase the noise. The gain bandwidth product is determined by C1, C2 and the preamp transconductance which increases with programmed gain. Therefore, the bandwidth does not drop proportionally to gain.

The input transistors Q1 and Q2 offer excellent matching, which is inherent in NPN bipolar transistors, as well as picoampere input bias current due to superbeta processing. The collector currents in Q1 and Q2 are held constant due to the feedback through the Q1-A1-R1 loop and Q2-A2-R2 loop which in turn impresses the differential input voltage across the external gain set resistor R_G. Since the current that flows through R_G also flows through R1 and R2, theratios provide agained-up differential voltage, $G = (R1 + R2)/R_G$, to the unity-gain difference amplifier A3. The common mode voltage is removed by A3, resulting in a single-ended output voltage referenced to the voltage on the REF pin. The resulting gain equation is:

$$V_{OUT} - V_{REF} = G(V_{IN}^+ - V_{IN}^-)$$

where:

 $G = (49.4 k\Omega / R_G) + 1$

solving for the gain set resistor gives:

 $R_{G} = 49.4 k\Omega / (G - 1)$



THEORY OF OPERATION

Input and Output Offset Voltage

The offset voltage of the LT1167 has two components: the output offset and the input offset. The total offset voltage referred to the input (RTI) is found by dividing the output offset by the programmed gain (G) and adding it to the input offset. At high gains the input offset voltage dominates, whereas at low gains the output offset voltage dominates. The total offset voltage is:

Total input offset voltage (RTI) = input offset + (output offset/G)

Total output offset voltage (RTO) = (input offset • G) + output offset

Reference Terminal

The reference terminal is one end of one of the four 10k resistors around the difference amplifier. The output voltage of the LT1167 (Pin 6) is referenced to the voltage on the reference terminal (Pin 5). Resistance in series with the REF pin must be minimized for best common mode rejection. For example, a 2Ω resistance from the REF pin to ground will not only increase the gain error by 0.02% but will lower the CMRR to 80dB.

Single Supply Operation

For single supply operation, the REF pin can be at the same potential as the negative supply (Pin 4) provided the output of the instrumentation amplifier remains inside the specified operating range and that one of the inputs is at least 2.5V above ground. The barometer application on the front page of this data sheet is an example that satisfies these conditions. The resistance R_b from the bridge transducer to ground sets the operating current for the bridge and also has the effect of raising the input common mode voltage. The output of the LT1167 is always inside the specified range since the barometric pressure rarely goes low enough to cause the output to rail (30.00 inches of Hg corresponds to 3.000V). For applications that require the output to swing at or below the REF potential, the voltage on the REF pin can be level shifted. An op amp is used to buffer the voltage on the REF pin since a parasitic series resistance will degrade the CMRR. The application in the back of this data sheet, Four Digit Pressure Sensor, is an example.

Output Offset Trimming

The LT1167 is laser trimmed for low offset voltage so that no external offset trimming is required for most applications. In the event that the offset needs to be adjusted, the circuit in Figure 2 is an example of an optional offset adjust circuit. The op amp buffer provides a low impedance to the REF pin where resistance must be kept to minimum for best CMRR and lowest gain error.

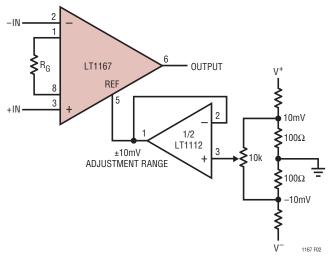
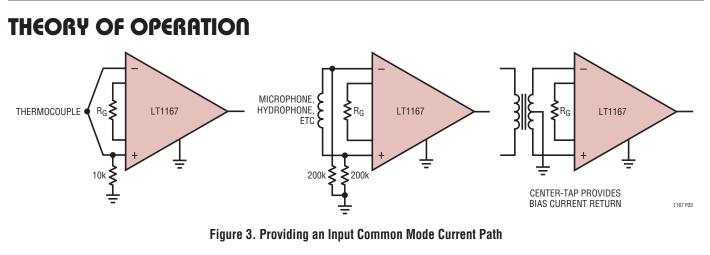


Figure 2. Optional Trimming of Output Offset Voltage

Input Bias Current Return Path

The low input bias current of the LT1167 (350pA) and the high input impedance (200G Ω) allow the use of high impedance sources without introducing additional offset voltage errors, even when the full common mode range is required. However, a path must be provided for the input bias currents of both inputs when a purely differential signal is being amplified. Without this path the inputs will float to either rail and exceed the input common mode range of the LT1167, resulting in a saturated input stage. Figure 3 shows three examples of an input bias current path. The first example is of a purely differential signal source with a $10k\Omega$ input current path to ground. Since the impedance of the signal source is low, only one resistor is needed. Two matching resistors are needed for higher impedance signal sources as shown in the second example. Balancing the input impedance improves both common mode rejection and DC offset. The need for input resistors is eliminated if a center tap is present as shown in the third example.





The LT1167 is a low power precision instrumentation amplifier that requires only one external resistor to accurately set the gain anywhere from 1 to 1000. The output can handle capacitive loads up to 1000pF in any gain configuration and the inputs are protected against ESD strikes up to 13kV (human body).

Input Current at High Common Mode Voltage

When operating within the specified input common mode range, both the LT1167 and LT1167-1 operate as shown in the Input Bias Current vs Common Mode Input Voltage graph shown in the Typical Performance Characteristics. If however the inputs are within approximately 0.8V of the positive supply, the LT1167 input current will increase to approximately -1μ A to -3μ A. If the impedance of the circuit driving the LT1167 inputs is sufficiently high (e.g., $10M\Omega$ when +V_S = 15V), this increased input current can pull the input voltage sufficiently high to keep the elevated input current flowing. The LT1167-1 has been modified so that the input current is typically two orders of magnitude lower under similar conditions. The LT1167-1 is recommended for new designs where input impedance is high.

Input Protection

The LT1167 can safely handle up to ± 20 mA of input current in an overload condition. Adding an external 5k input resistor in series with each input allows DC input fault voltages up to ± 100 V and improves the ESD immunity to 8kV (contact) and 15kV (air discharge), which is the IEC 1000-4-2 level 4 specification. If lower value input

resistors are needed, a clamp diode from the positive supply to each input will maintain the IEC 1000-4-2 specification to level 4 for both air and contact discharge. A 2N4393 drain/source to gate is a good low leakage diode for use with 1k resistors, see Figure 4. The input resistors should be carbon and not metal film or carbon film.

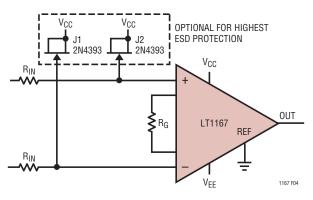


Figure 4. Input Protection

RFI Reduction

In many industrial and data acquisition applications, instrumentation amplifiers are used to accurately amplify small signals in the presence of large common mode voltages or high levels of noise. Typically, the sources of these very small signals (on the order of microvolts or millivolts) are sensors that can be a significant distance from the signal conditioning circuit. Although these sensors may be connected to signal conditioning circuitry, using shielded or unshielded twisted-pair cabling, the cabling may act as antennae, conveying very high frequency interference directly into the input stage of the LT1167.



The amplitude and frequency of the interference can have an adverse effect on an instrumentation amplifier's input stage by causing an unwanted DC shift in the amplifier's input offset voltage. This well known effect is called RFI rectification and is produced when out-of-band interference is coupled (inductively, capacitively or via radiation) and rectified by the instrumentation amplifier's input transistors. These transistors act as high frequency signal detectors, in the same way diodes were used as RF envelope detectors in early radio designs. Regardless of the type of interference or the method by which it is coupled into the circuit, an out-of-band error signal appears in series with the instrumentation amplifier's inputs.

To significantly reduce the effect of these out-of-band signals on the input offset voltage of instrumentation amplifiers, simple lowpass filters can be used at the inputs. These filters should be located very close to the input pins of the circuit. An effective filter configuration is illustrated in Figure 5, where three capacitors have been added to the inputs of the LT1167. Capacitors C_{XCM1} and C_{XCM2} form lowpass filters with the external series resistors $R_{S1, 2}$ to any out-of-band signal appearing on each of the input traces. Capacitor C_{XD} forms a filter to reduce any unwanted signal that would appear across the input traces. An added benefit to using C_{XD} is that the circuit's AC common mode rejection is not degraded due to common mode capacitive

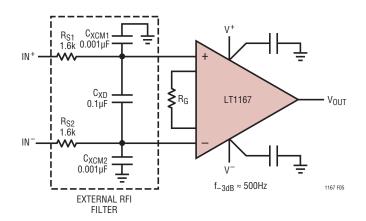


Figure 5. Adding a Simple RC Filter at the Inputs to an Instrumentation Amplifier Is Effective in Reducing Rectification of High Frequency Out-of-Band Signals

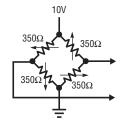
imbalance. The differential mode and common mode time constants associated with the capacitors are:

 $t_{DM(LPF)} = (2)(R_S)(C_{XD})$ $t_{CM(LPF)} = (R_{S1, 2})(C_{XCM1, 2})$

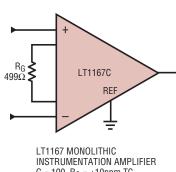
Setting the time constants requires a knowledge of the frequency, or frequencies of the interference. Once this frequency is known, the common mode time constants can be set followed by the differential mode time constant. To avoid any possibility of inadvertently affecting the signal to be processed, set the common mode time constant an order of magnitude (or more) larger than the differential mode time constant. Set the common mode time constants such that they do not degrade the LT1167's inherent AC CMR. Then the differential mode time constant can be set for the bandwidth required for the application. Setting the differential mode time constant close to the sensor's BW also minimizes any noise pickup along the leads. To avoid any possibility of common mode to differential mode signal conversion, match the common mode time constants to 1% or better. If the sensor is an RTD or a resistive strain gauge, then the series resistors $R_{S1,2}$ can be omitted, if the sensor is in proximity to the instrumentation amplifier.

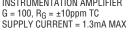
"Roll Your Own"—Discrete vs Monolithic LT1167 Error Budget Analysis

The LT1167 offers performance superior to that of "roll your own" three op amp discrete designs. A typical application that amplifies and buffers a bridge transducer's differential output is shown in Figure 6. The amplifier, with its gain set to 100, amplifies a differential, full-scale output voltage of 20mV over the industrial temperature range. To make the comparison challenging, the low cost version of the LT1167 will be compared to a discrete instrumentation amp made with the A grade of one of the best precision quad op amps, the LT1114A. The LT1167C outperforms the discrete amplifier that has lower V_{OS}, lower I_B and comparable V_{OS} drift. The error budget comparison in Table 1 shows how various errors are calculated and how each error affects the total error budget. The table shows the greatest differences between the discrete solution and



PRECISION BRIDGE TRANSDUCER





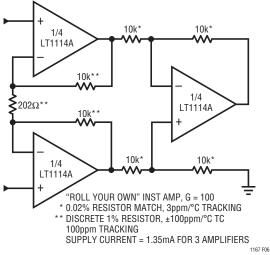


Figure 6. "Roll Your Own" vs LT1167

Table 1. "Roll Your Own" vs LT1167 Error Budget

| | | "ROLL YOUR OWN"' CIRCUIT | ERROR, | ppm OF FULL SCALE |
|--|---|---|------------------------------------|-----------------------------------|
| ERROR SOURCE | LT1167C CIRCUIT CALCULATION | CALCULATION | LT1167C | "ROLL YOUR OWN" |
| Absolute Accuracy at $T_A = 25^{\circ}C$ Input Offset Voltage, μV Output Offset Voltage, μV Input Offset Current, nA CMR, dB | 60μV/20mV (300μV/100)/20mV [(450pA)(350/2)Ω]/20mV 110dB→[(3.16ppm)(5V)]/20mV | 100μV/20mV [(60μV)(2)/100]/20mV [(450pA)(350Ω)/2]/20mV [(0.02% Match)(5V)]/20mV | 3000 150 4 790 | 5000 60 4 500 |
| Drift to 85°C Gain Drift, ppm/°C Input Offset Voltage Drift, μV/°C Output Offset Voltage Drift, μV/°C | (50ppm + 10ppm)(60°C) [(0.4µV/°C)(60°C)]/20mV [(6µV/°C)(60°C)]/100/20mV | Total Absolute Error (100ppm/°C Track)(60°C) [(1.6µV/°C)(60°C)]/20mV [(1.1µV/°C)(2)(60°C)]/100/20mV | 3944 3600 1200 180 | 5564 6000 4800 66 |
| Resolution Gain Nonlinearity, ppm of Full Scale Typ 0.1Hz to 10Hz Voltage Noise, µV _{P-P} | 15ppm 0.28µV _{P-P} /20mV | Total Drift Error 10ppm (0.3µV _{P-P})(√2)/20mV | 4980 15 14 | 10866 10 21 |
| | | Total Resolution Error Grand Total Error | 29 8953 | 31 16461 |

 $G = 100, VS = \pm 15V$

All errors are min/max and referred to input.

the LT1167 are input offset voltage and CMRR. Note that for the discrete solution, the noise voltage specification is multiplied by $\sqrt{2}$ which is the RMS sum of the uncorelated noise of the two input amplifiers. Each of the amplifier errors is referenced to a full-scale bridge differential voltage of 20mV. The common mode range of the bridge is 5V. The LT1114 data sheet provides offset voltage, offset voltage drift and offset current specifications for the matched op amp pairs used in the error-budget table. Even with an excellent matched op amp like the LT1114, the discrete solution's total error is significantly higher than the LT1167's total error. The LT1167 has additional advantages over the discrete design, including lower component cost and smaller size.

Current Source

Figure 7 shows a simple, accurate, low power programmable current source. The differential voltage across Pins 2 and 3 is mirrored across R_G . The voltage across R_G is amplified and applied across R_X , defining the output current. The 50µA bias current flowing from Pin 5 is buffered by the LT1464 JFET operational amplifier. This



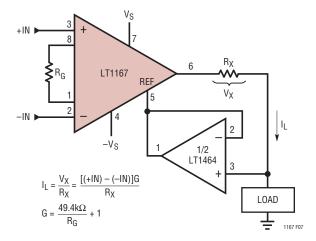


Figure 7. Precision Voltage-to-Current Converter

has the effect of improving the resolution of the current source to 3pA, which is the maximum I_B of the LT1464A. Replacing R_G with a programmable resistor greatly increases the range of available output currents.

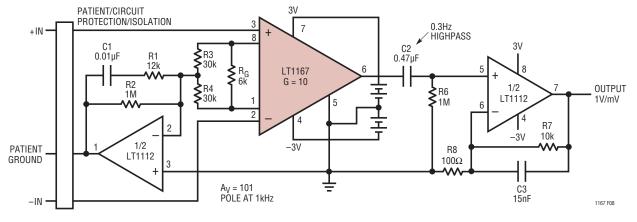
Nerve Impulse Amplifier

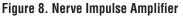
The LT1167's low current noise makes it ideal for high source impedance EMG monitors. Demonstrating the LT1167's ability to amplify low level signals, the circuit in Figure 8 takes advantage of the amplifier's high gain and low noise operation. This circuit amplifies the low level nerve impulse signals received from a patient at Pins 2 and 3. R_G and the parallel combination of R3 and R4 set a gain of ten. The potential on LT1112's Pin 1 creates a ground for the common mode signal. C1 was chosen to maintain the stability of the patient ground. The LT1167's

high CMRR ensures that the desired differential signal is amplified and unwanted common mode signals are attenuated. Since the DC portion of the signal is not important, R6 and C2 make up a 0.3Hz highpass filter. The AC signal at LT1112's Pin 5 is amplified by a gain of 101 set by (R7/R8) +1. The parallel combination of C3 and R7 form a lowpass filter that decreases this gain at frequencies above 1kHz. The ability to operate at \pm 3V on 0.9mA of supply current makes the LT1167 ideal for battery-powered applications. Total supply current for this application is 1.7mA. Proper safeguards, such as isolation, must be added to this circuit to protect the patient from possible harm.

Low ${\rm I}_{\rm B}$ Favors High Impedance Bridges, Lowers Dissipation

The LT1167's low supply current, low supply voltage operation and low input bias currents optimize it for battery-powered applications. Low overall power dissipation necessitates using higher impedance bridges. The single supply pressure monitor application (Figure 9) shows the LT1167 connected to the differential output of a 3.5k bridge. The bridge's impedance is almost an order of magnitude higher than that of the bridge used in the error-budget table. The picoampere input bias currents keep the error caused by offset current to a negligible level. The LT112 level shifts the LT1167's reference pin and the ADC's analog ground pins above ground. The LT1167's and LT1112's combined power dissipation is still less than the bridge's. This circuit's total supply current is just 2.8mA.







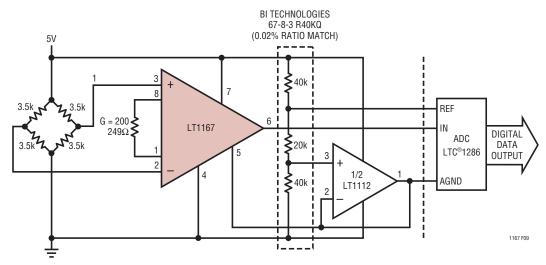
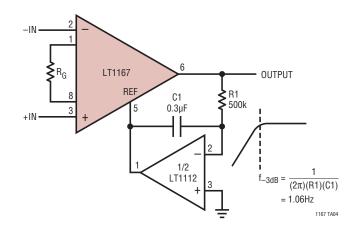


Figure 9. Single Supply Bridge Amplifier

TYPICAL APPLICATION

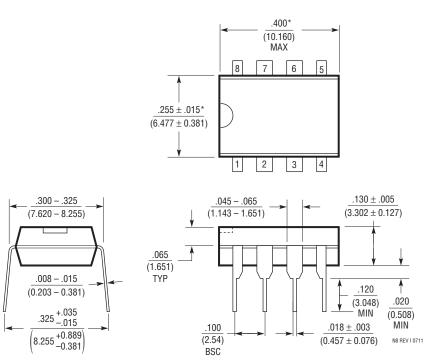
AC Coupled Instrumentation Amplifier





PACKAGE DESCRIPTION

Please refer to http://www.linear.com/designtools/packaging/ for the most recent package drawings.



N8 Package 8-Lead PDIP (Narrow .300 Inch) (Reference LTC DWG # 05-08-1510 Rev I)

NOTE:

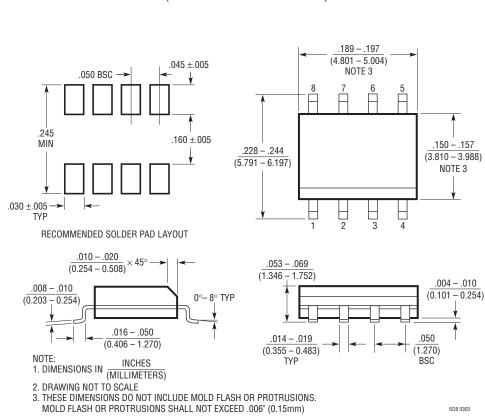
INCHES 1. DIMENSIONS ARE MILLIMETERS

*THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED .010 INCH (0.254mm)



PACKAGE DESCRIPTION

Please refer to http://www.linear.com/designtools/packaging/ for the most recent package drawings.



S8 Package 8-Lead Plastic Small Outline (Narrow .150 Inch) (Reference LTC DWG # 05-08-1610)



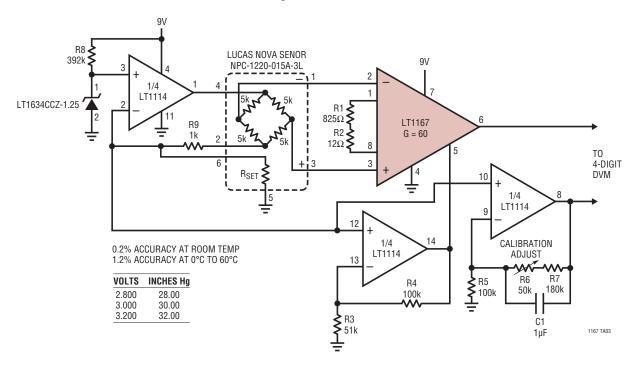
REVISION HISTORY (Revision history begins at Rev B)

| REV | DATE | DESCRIPTION | PAGE NUMBER |
|-----|-------|---|-------------|
| В | 01/11 | Added LT1167-1 to Description, Absolute Maximum Ratings, Order Information, Electrical Characteristics and Applications Information Section | 1-6, 15 |
| С | 08/11 | Correction to TYP specification for SR from 12 to 1.2 | 4 |
| | | Columns shifted to left in CMRR specification | 4, 5 |



TYPICAL APPLICATION

4-Digit Pressure Sensor



RELATED PARTS

| PART NUMBER | DESCRIPTION | COMMENTS |
|-------------|---|---|
| LTC1100 | Precision Chopper-Stabilized Instrumentation Amplifier | Best DC Accuracy |
| LT1101 | Precision, Micropower, Single Supply Instrumentation Amplifier | Fixed Gain of 10 or 100, I _S < 105µA |
| LT1102 | High Speed, JFET Instrumentation Amplifier | Fixed Gain of 10 or 100, 30V/µs Slew Rate |
| LT1168 | Low Power, Single Resistor Programmable Instrumentation Amplifier | I _{SUPPLY} = 530μA Max |
| LTC1418 | 14-Bit, Low Power, 200ksps ADC with Serial and Parallel I/O | Single Supply 5V or ±5V Operation, ±1.5LSB INL and ±1LSB DNL Max |
| LT1460 | Precision Series Reference | Micropower; 2.5V, 5V, 10V Versions; High Precision |
| LT1468 | 16-Bit Accurate Op Amp, Low Noise Fast Settling | 16-Bit Accuracy at Low and High Frequencies, 90MHz GBW, 22V/µs, 900ns Settling |
| LTC1562 | Active RC Filter | Lowpass, Bandpass, Highpass Responses; Low Noise, Low Distortion, Four 2nd Order Filter Sections |
| LTC1605 | 16-Bit, 100ksps, Sampling ADC | Single 5V Supply, Bipolar Input Range: ±10V, Power Dissipation: 55mW Typ |





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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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